

ABSTRACT OF THE DISCLOSURE

A solid-state imaging device is able to prevent a sensitivity from being lowered and to suppress a smear caused as a pixel size is reduced and to provide an excellent image quality even though it is miniaturized and a manufacturing method thereof is proposed.

Also, a method of manufacturing a semiconductor device is able to form a conductive layer having an excellent adhesion with an underlayer and whose surface has an excellent flatness in the process for forming a metal interconnection and the process for burying a contact-hole. A solid-state imaging device (20) includes a light-shielding film (6) of a two layer structure comprising a first film (11) formed of a film deposited by a sputtering or vapor deposition and a second film (12) formed of a tungsten film deposited by a chemical vapor deposition.

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